



## Synthesis of epitaxial monolayer Janus SPtSe

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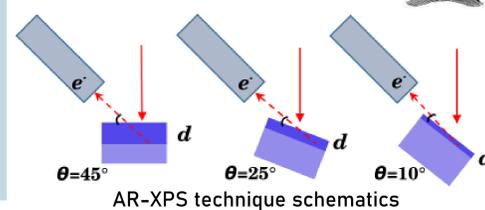
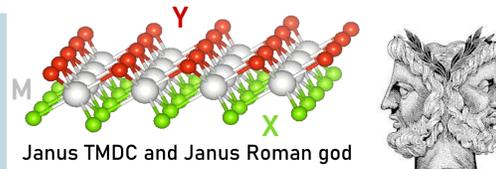
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### Janus Transition Metal Dichalcogenides (TMDCs)

Monolayer TMDCs whose chalcogen layers are of different chemical nature (e.g. XMY, M=metal, X=Se and Y=S) are said **Janus** after the **biface** Roman god<sup>1</sup>. They can be prepared by selectively substituting the chalcogen atoms in the pristine TMDC topmost layer by annealing the material in a suitable gaseous precursor atmosphere of another chalcogen species. It turns out that the vertical mirror symmetry in the Janus TMDC is broken.

By *operando in situ* grazing incidence X-ray diffraction (GIXRD) at the BM32 beamline at ESRF, we could follow the structural transformation of a TMDC into a Janus material during the substitution process. Thanks to angle resolved X-ray photoemission (AR-XPS) our analysis is sensitive to the chemical depth profile.



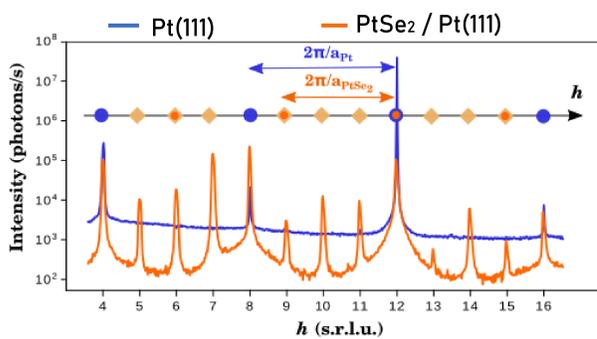
Diffractometer + MBE chamber @BM32

### Growth of PtSe<sub>2</sub> by selenization of Pt(111)<sup>3</sup>

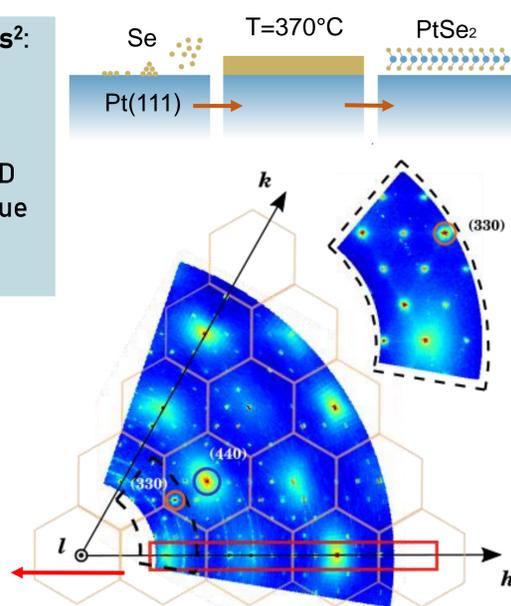
PtSe<sub>2</sub> is grown on Pt(111) by a **two-steps process**<sup>2</sup>:

- 1) Se deposition on Pt(111)
- 2) Annealing at 370°C

The as-grown PtSe<sub>2</sub> shows a very intense GIXRD pattern with a commensurate **superstructure** due to the exact **3:4** mismatch between Pt(111) and PtSe<sub>2</sub> lattice constants.

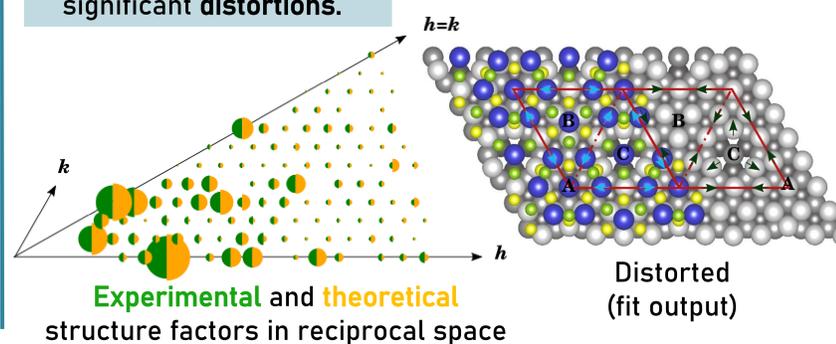
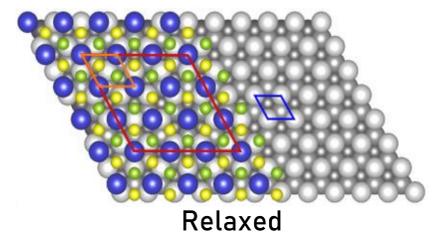


Radial scan and in-plane sector map of the reciprocal space after PtSe<sub>2</sub> growth



Our fitting and modelling of the GIXRD data shows that :

- PtSe<sub>2</sub> is **strained** (0.7%)
- The **interface coupling is strong** (not Van der Waals!); both PtSe<sub>2</sub> and Pt(111) layers undergo significant **distortions**.



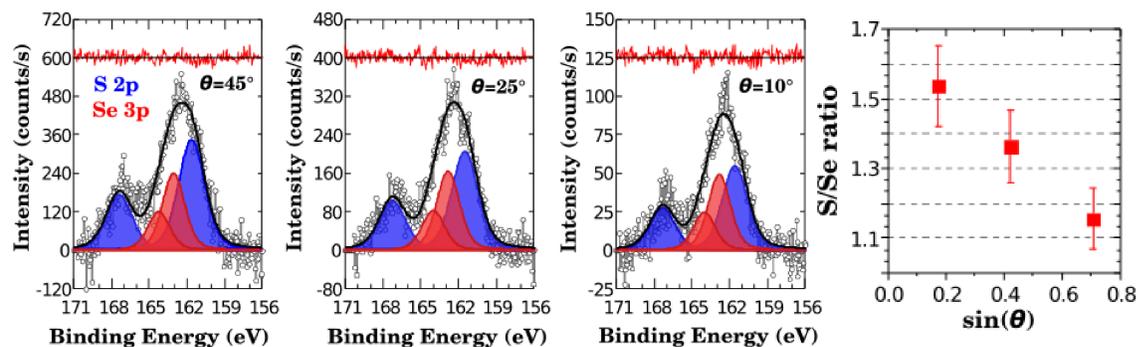
### Transformation of PtSe<sub>2</sub> into Janus SePtS by sulfurization in H<sub>2</sub>S atmosphere<sup>4</sup>

Se in PtSe<sub>2</sub> can be replaced by S by supplying H<sub>2</sub>S gas at a suitable temperature (**sulfurization**) :

I - a pre-annealing in vacuum creates defects and vacancies in PtSe<sub>2</sub>.

II - H<sub>2</sub>S supplies S to replace Se.

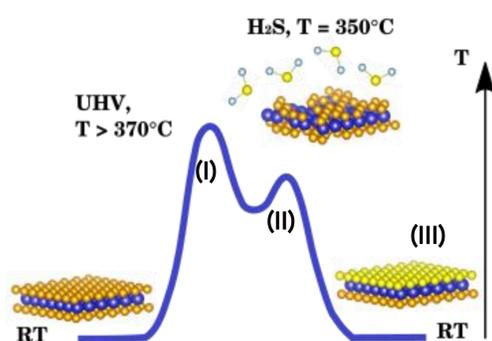
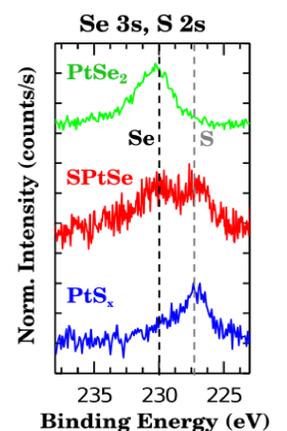
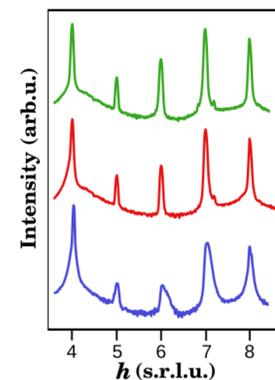
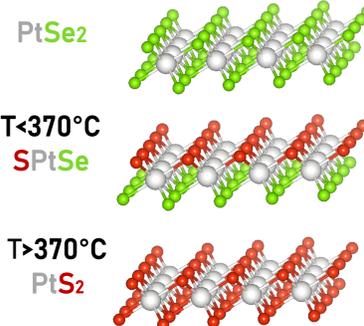
III - Suitable T allows Se-by-S substitution in the top chalcogen layer but not in the bottom one.



AR-XPS determines that the substitution occurs mostly at the **topmost** surface and S signal comes mostly from **one** layer.

- **Higher T** leads to Se-by-S substitution also in the **bottom** layer.

- The diffraction pattern does not change during the sulfurization. The Janus TMDC is **isostructural** with the pristine PtSe<sub>2</sub>.



#### CONTACT PERSON

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#### REFERENCES

- <sup>1</sup>Lu, A.-Y., et al., "Janus monolayers of transition metal dichalcogenides", *Nat. Nanotech.*, 2017.
- <sup>2</sup>Wang, Y., et al., "Monolayer PtSe<sub>2</sub>, a new semiconducting transition-metal dichalcogenide ...", *Nano Lett.*, 2015.
- <sup>3</sup>Sant, R., "Synchrotron x-ray exploration of growth and structure in 2D dichalcogenides", *PhD Thesis*, 2019
- <sup>4</sup>Sant, R., et al. "Synthesis of epitaxial monolayer Janus SPtSe.", *submitted*, 2020.